

ISOTOP[®] Boost chopper High speed Trench + Field Stop IGBT4

$V_{CES} = 1200V$

$I_{\rm C} = 40 {\rm A}$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - RBSOA and SCSOA rated
 - SiC Schottky Diode (CR1)
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
 - ISOTOP[®] Package (SOT-227)
 - Very low stray inductance
 - High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
I _C	Continuous Collector Current	$T_C = 80^{\circ}C$	40	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	160	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	80A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APT40GLQ120JCU2 - Rev 0 November, 2012





Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				25	μA
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 40A$	$T_j = 25^{\circ}C$	1.7	2.05	2.4	v
			$T_{j} = 150^{\circ}C$		2.6		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				120	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			2300		
C _{oes}	Output Capacitance	$V_{CE} = 25V$			150		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz			130		
Q _G	Gate charge	$V_{GE} = 15V, I_C = V_{CE} = 960V$	40A		185		nC
T _{d(on)}	Turn-on Delay Time	Resistive Switch	ing (25°C)		30		ns
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{GE} = 600V$			57		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 40A$			290		
T _f	Fall Time	$R_G = 12\Omega$			16		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 40A$ $R_G = 12\Omega$			30		
Tr	Rise Time				49		ns
T _{d(off)}	Turn-off Delay Time				366		
$T_{\rm f}$	Fall Time				48		
Б	Turn on Switching Energy	$V_{GE} = \pm 15V$	$T_i = 25^{\circ}C$		1.9		
Eon	Turn-on Switching Energy	$V_{Bus} = 600 V$	$T_{i} = 150^{\circ}C$		2.25		mJ
E _{off}	Turn-off Switching Energy	$I_C = 40A$	$T_i = 25^{\circ}C$		1.2		1113
Loff	Turn-on Switching Ellergy	$R_G = 12\Omega$	$T_{i} = 150^{\circ}C$		2.25		
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 600V$ $t_p \le 10\mu s$; $T_i = 150^{\circ}C$			150		А

Chopper SiC diode ratings and characteristics (CR1)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
т	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$		64	400	۸
I _{RM}			$T_{j} = 175^{\circ}C$		112	2000	μA
$I_{\rm F}$	DC Forward Current		$Tc = 100^{\circ}C$		20		А
V _F	Diode Forward Voltage	$I_{\rm p} = 20 \Delta$	$T_i = 25^{\circ}C$		1.6	1.8	V
▼ F			$T_1 = 175^{\circ}C$		2.3	3	v
Qc	Total Capacitive Charge	$I_F = 20A, V_R = 600V$ di/dt =1000A/µs			80		nC
С	Total Capacitance	$f = 1 MHz, V_R = 200 V$			192		pF
C		$f = 1 MHz, V_R =$	400V		138		hr

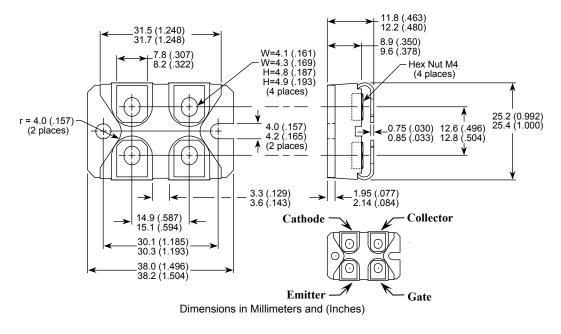
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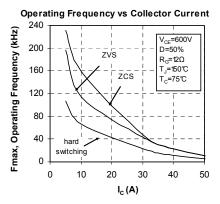
Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.48	°C/W
		SiC Diode			0.8	
R _{thJA}	Junction to Ambient (IGBT & Diode)				20	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V
T_J, T_{STG}	Storage Temperature Range		-55		150	°C
$T_{\rm L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	C
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

SOT-227 (ISOTOP[®]) Package Outline

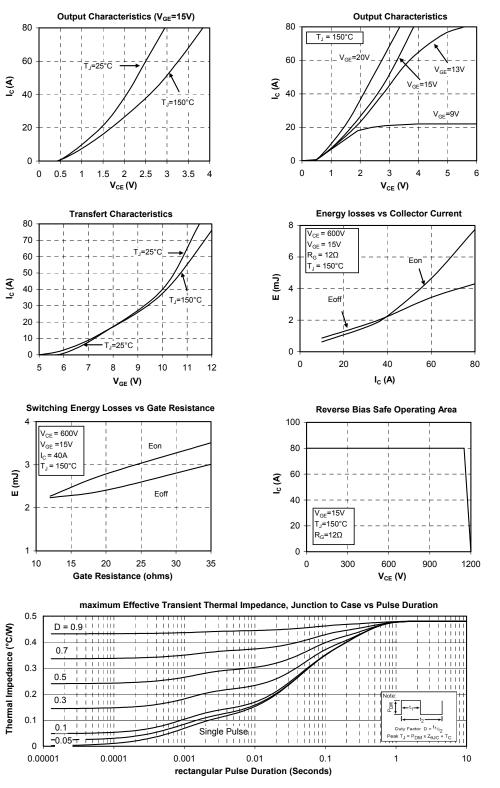


Typical IGBT Performance Curve



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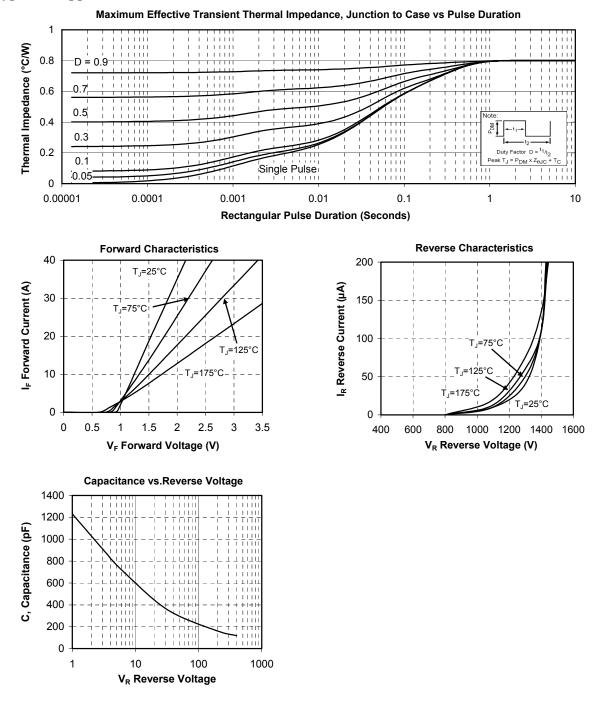




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Typical chopper SiC diode Performance Curve



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